



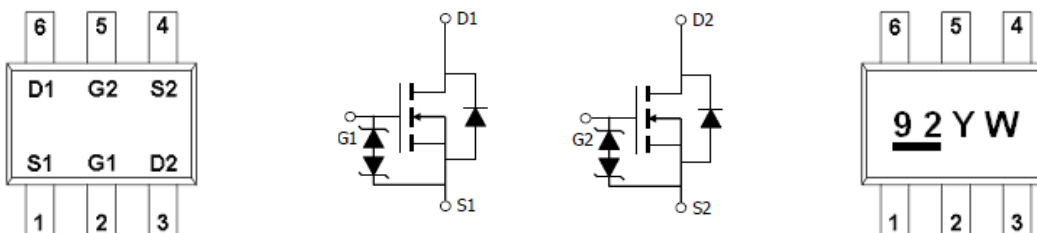
## General Description

AFN1932E, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent  $R_{DS(ON)}$ , low gate charge. These devices are particularly suited for low voltage power management, such as smart phone and notebook computer, and low in-line power loss are needed in commercial industrial surface mount applications.

## Features

- 30V/1.8A,  $R_{DS(ON)}=450m\Omega@V_{GS}=4.5V$
- 30V/1.5A,  $R_{DS(ON)}=600m\Omega@V_{GS}=2.5V$
- Low Offset (Error) Voltage
- Low-Voltage Operation
- High-Speed Circuits
- Low Battery Voltage Operation
- **ESD Protected**
- SOT-363 package design

## Pin Description ( SOT-363 )



## Application

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories
- Battery Operated Systems
- Load/Power Switching Smart Phones, Pagers
- PA Switch
- Level Switch

## Pin Define

Pin	Symbol	Description
1	S1	Source 1
2	G1	Gate 1
3	D2	Drain 2
4	S2	Source 2
5	G2	Gate 2
6	D1	Drain1

## Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFN1932ES36RG	92YW	SOT-363	Tape & Reel	3000 EA

- ※ 92 parts code
- ※ Y year code ( 0 ~ 9 )
- ※ W week code ( A ~ Z = 1 ~ 26 / a ~ z = 27 ~ 52 )
- ※ AFN1932ES36RG : 7" Tape & Reel ; Pb- Free ; Halogen -Free



**Absolute Maximum Ratings**

(T<sub>A</sub>=25°C Unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	30	V
Gate –Source Voltage	V <sub>GSS</sub>	±12	V
Continuous Drain Current(T <sub>J</sub> =150°C)	I <sub>D</sub>	T <sub>A</sub> =25°C	1.8
		T <sub>A</sub> =70°C	1.0
Pulsed Drain Current	I <sub>DM</sub>	6	A
Continuous Source Current(Diode Conduction)	I <sub>S</sub>	1	A
Power Dissipation	P <sub>D</sub>	T <sub>A</sub> =25°C	0.3
		T <sub>A</sub> =70°C	0.2
Operating Junction Temperature	T <sub>J</sub>	-55/150	°C
Storage Temperature Range	T <sub>STG</sub>	-55/150	°C

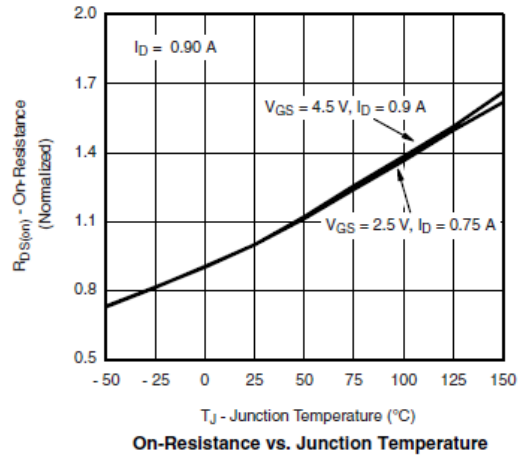
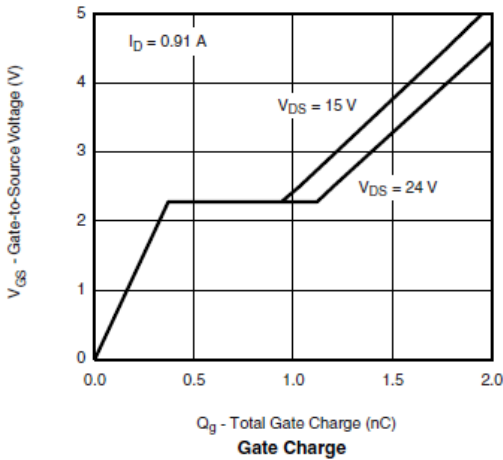
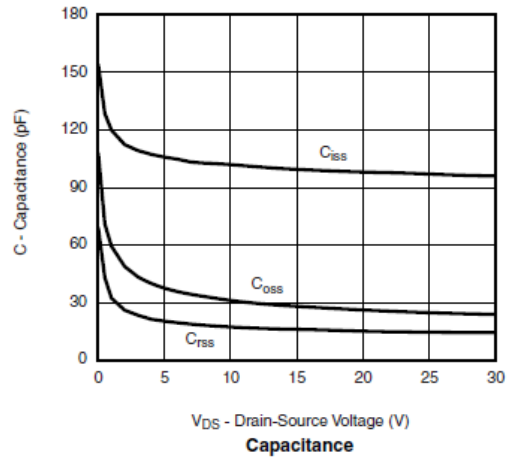
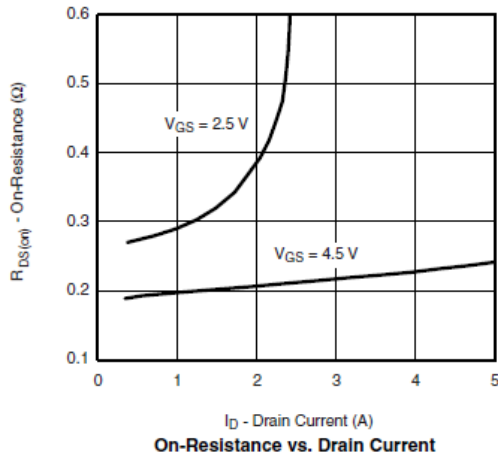
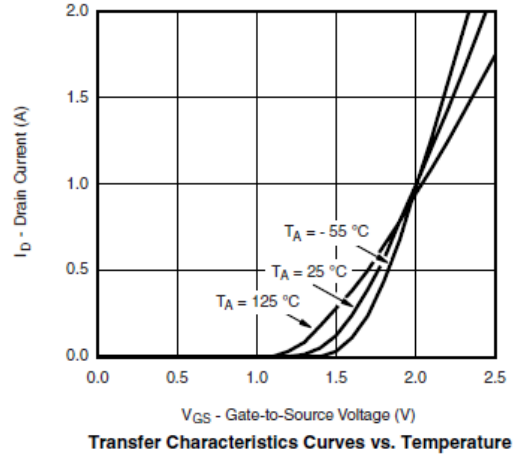
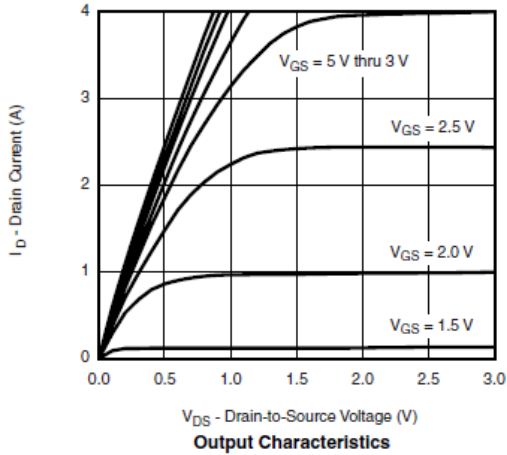
**Electrical Characteristics**

(T<sub>A</sub>=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	30			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	0.85	1.1	1.35	V
Gate Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±12V			±10	mA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V			1	uA
		V <sub>DS</sub> =24V, V <sub>GS</sub> =0V T <sub>J</sub> =85°C			5	
On-State Drain Current	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5V, V <sub>GS</sub> =4.5V	1.8			A
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =1.8A		400	450	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =1.5A		525	600	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1.0A		1		S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1.0A, V <sub>GS</sub> =0V		0.65	1.2	V
<b>Dynamic</b>						
Input Capacitance	C <sub>iSS</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V f=1MHz		85		pF
Output Capacitance	C <sub>oss</sub>			25		
Reverse Transfer Capacitance	C <sub>rss</sub>			15		
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =4.5V I <sub>D</sub> ≡1.2A		1.4	1.8	nC
Gate-Source Charge	Q <sub>gs</sub>			0.3		
Gate-Drain Charge	Q <sub>gd</sub>			0.6		
Turn-On Time	t <sub>d(on)</sub>	V <sub>DD</sub> =15V, R <sub>L</sub> =20Ω I <sub>D</sub> ≡1.2A, V <sub>GEN</sub> =4.5V R <sub>G</sub> =1Ω		15	25	ns
	t <sub>r</sub>			25	45	
Turn-Off Time	t <sub>d(off)</sub>			15	25	
	t <sub>f</sub>			10	20	

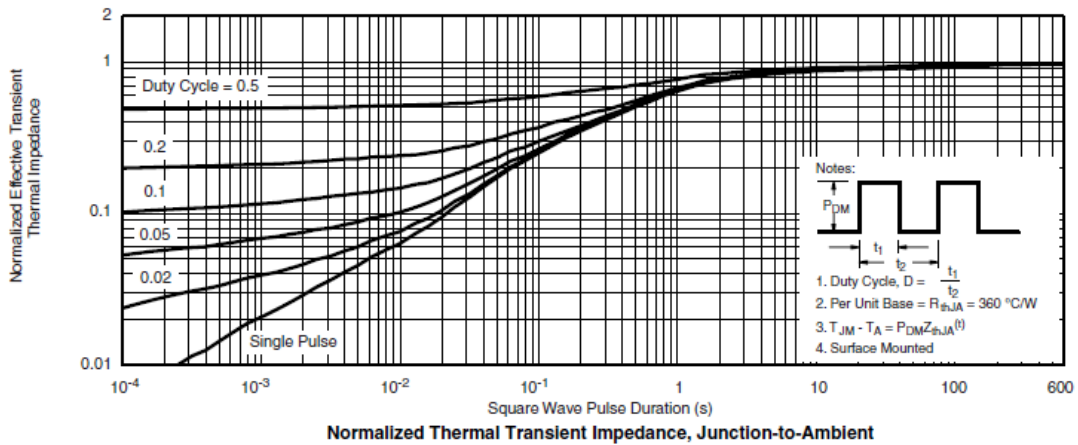
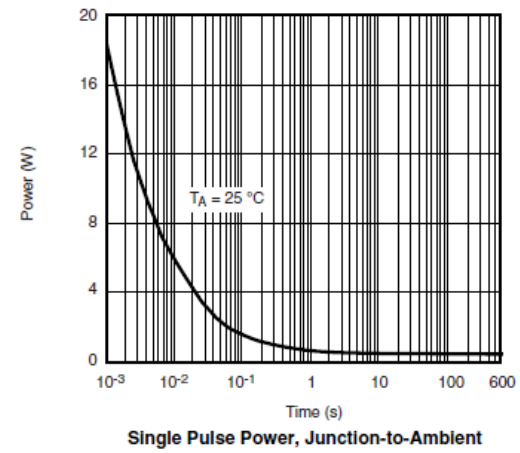
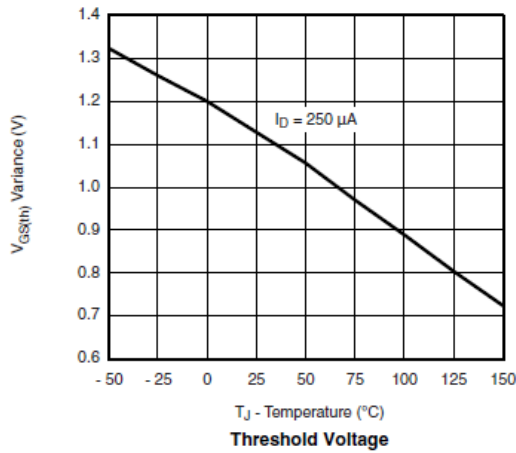
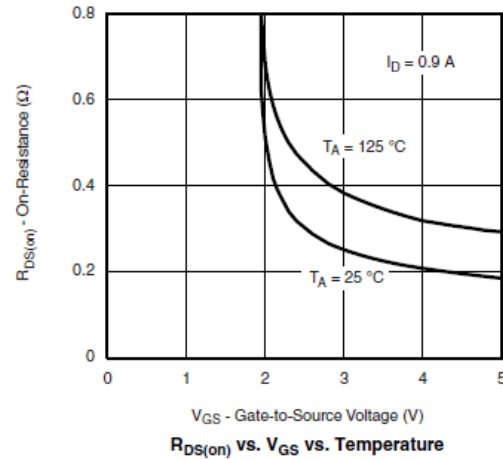
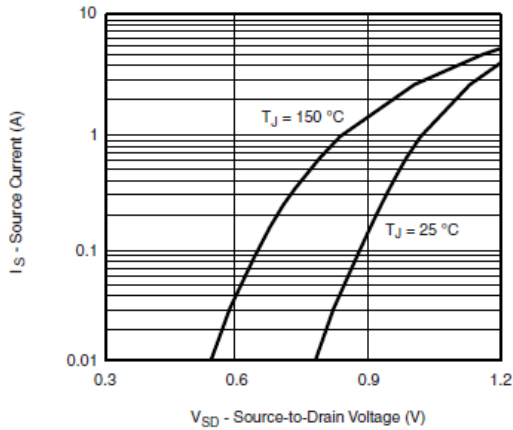


## Typical Characteristics





## Typical Characteristics





**Typical Characteristics**

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

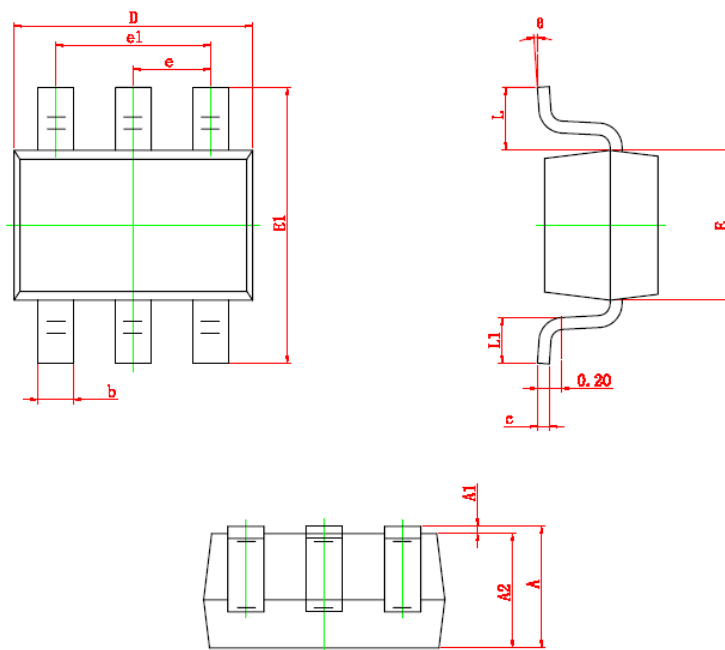


Unclamped Inductive Switching Test Circuit & Waveforms





**Package Information ( SOT-363 )**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

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